

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	22	diffusive adj metal	USPAT; US-PGPUB	2002/09/05 10:49
2	BRS	2	("3249728" "3671702").PN.	USPAT	2002/09/05 11:01
3	BRS	15	4105828.URPN.	USPAT	2002/09/05 11:02
4	IS&R	871	(257/315).CCLS.	USPAT; US-PGPUB	2002/09/05 11:05
5	IS&R	0	("6 and (tft or (thin adj film)").PN.	USPAT; US-PGPUB	2002/09/05 11:06
6	IS&R	0	("6 and (tft or (thin adj film))").PN.	USPAT; US-PGPUB	2002/09/05 11:06
7	BRS	97	((257/315).CCLS.) and (tft or (thin adj film))	USPAT; US-PGPUB	2002/09/05 11:06
8	BRS	33	((257/315).CCLS.) and (tft or (thin adj film))) and ((silver or ag or v or vanadium) with gate)	USPAT; US-PGPUB	2002/09/05 11:15
9	BRS	12	((257/315).CCLS.) and ((silver or ag))	USPAT; US-PGPUB	2002/09/05 11:16
10	BRS	399	second adj floating adj gate	USPAT; US-PGPUB	2002/09/05 13:47

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6420752 B1	20020716	14	Semiconductor device with self-aligned contacts using a liner oxide layer	257/315	257/314; 365/185.01; 365/185.26	Ngo, Minh Van et al.
2	US 6229175 B1	20010508	24	Nonvolatile memory	257/315	257/298; 257/316; 257/317; 257/318; 257/320; 257/321	Uchida, Hidetsugu
3	US 5644528 A	19970701	18	Non-volatile memory having a cell applying to multi-bit data by multi-layered floating gate architecture and programming method for the same	365/185.03	365/185.01; 365/185.18	Kojima, Toshiaki
4	US 5517044 A	19960514	12	Non-volatile semiconductor memory device having thin film transistors equipped with floating gates	257/316	257/206; 257/317; 257/365; 257/401	Koyama, Shoji

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6420752 B1	20020716	14	Semiconductor device with self-aligned contacts using a liner oxide layer	257/315	257/314; 365/185.01; 365/185.26	Ngo, Minh Van et al.
2	US 6388285 B1	20020514	10	Ferromagnetic cell with internal oxygen source and method of oxygen release	257/315	257/310	Black, Charles Thomas et al.
3	US 6225668 B1	20010501	303	Semiconductor device having a single crystal gate electrode and insulation	257/368	257/296; 257/298; 257/300; 257/306; 257/310; 257/311; 257/315; 257/316; 257/317; 257/319	Shindo, Masahiro et al.
4	US 4939559 A	19900703	11	Dual electron injector structures using a conductive oxide between injectors	257/38	257/315	DiMaria, Donelli J. et al.

257/315 + Silver on Ag